

MAR 04 2005

REPLY UNDER 37 CFR 1.116
EXPEDITED PROCEDURE
TECHNOLOGY CENTER 2811

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:	Bruley, <i>et al.</i>	Conf. #:	2127
Serial No.:	10/605,128	Art Unit:	2814
Filed:	09/10/2003	Docket No.:	FIS920030230US1 (IBMF-0025)
Title:	CAPACITOR AND FABRICATION METHOD USING ULTRA-HIGH VACUUM CVD OF SILICON NITRIDE		
	Examiner:	Weiss, Howard	

COMMISSIONER FOR PATENTS

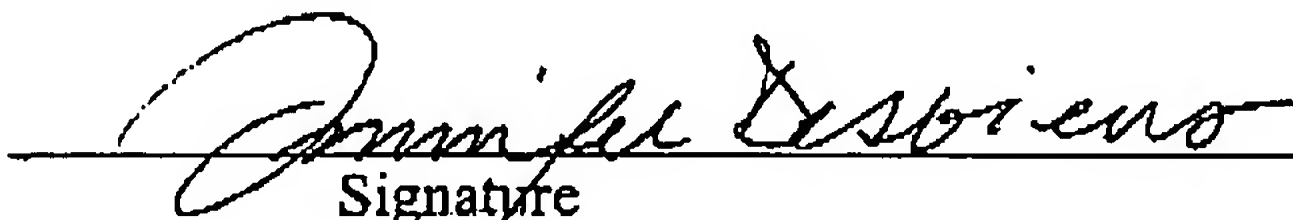
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Transmitted herewith is: After-Final Amendment in 7 pages
in the above identified application.

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AFTER-FINAL AMENDMENT

Sir:

I. INTRODUCTORY COMMENTS

In response to the final Office Action of January 5, 2005, please amend the above-referenced patent application as follows.

10/605,128

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